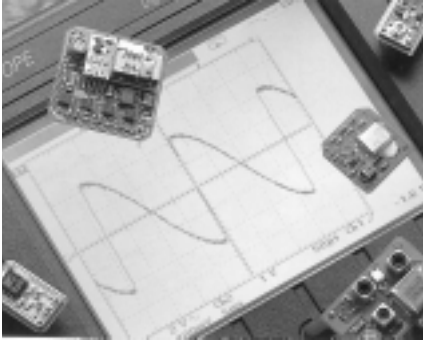


本記事 日本 CQ出版社가 發行 「トランジスタ技術」誌 著作権 協定 依據 提供 資料



3

大隅 明/小柳津 泰夫

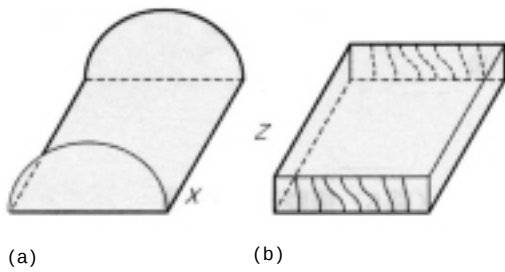
Q가

1880
가

가

가

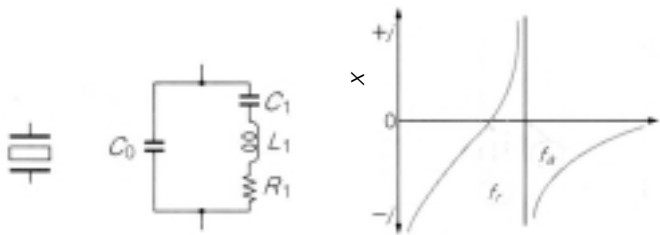
1881



1. AT

2. AT

($\Delta f / \Delta T = 0$)

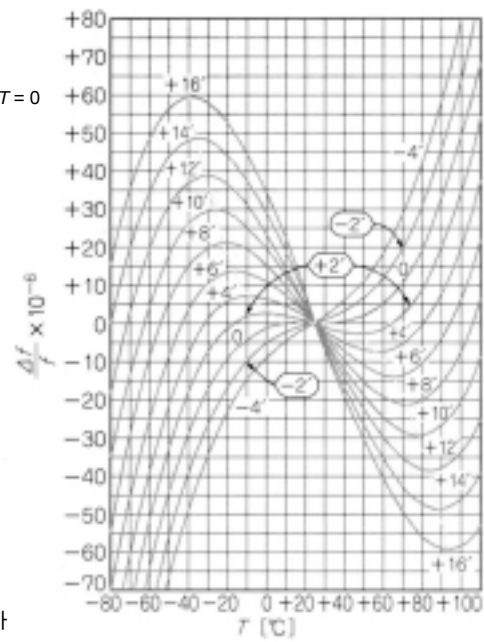


(a)

(b) 가

4.

가





가 Q가

(),

AT

(角)

(thickness sliding vibration)

AT

(水晶)

1(a) AT

1(b)

AT

(2) 3

가 100%

(autoclave) (種)

+5 ° X

1

2

가

3(a) IEC JIS

(雙

3(b) 가

f_s $L_1 C_1$

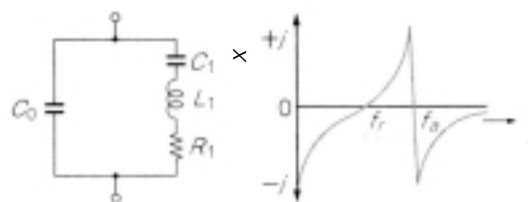
晶)

가

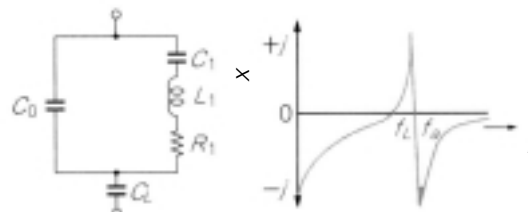
Q가

$$f_s = \frac{1}{2\pi\sqrt{L_1 C_1}}$$

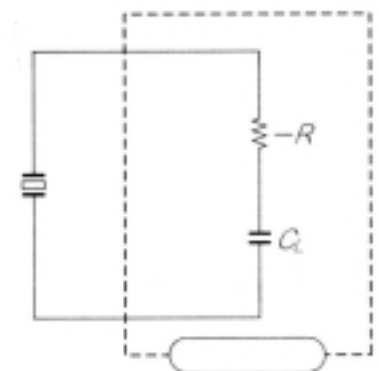
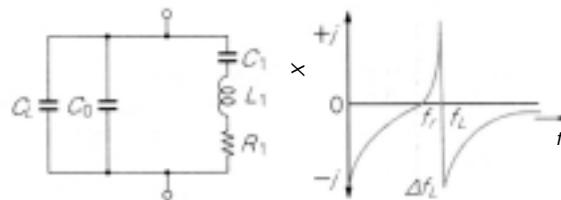
(a)



(b)



(c)



6.

5.

3/

, Q ,

$$Q = \frac{2\pi f_s L_1}{R_1} = \frac{1}{2\pi f_s R_1 C_1}$$

 C_L

VCXO

4

가

 C_0/C_1 C_0

5

7

7(a)

32.768kHz

7(b), (c)

AT

1M ~ 150MHz

SMD

6

(負性)

 $-R$ C_L $-R$ ()

SMD

SMD

SMD

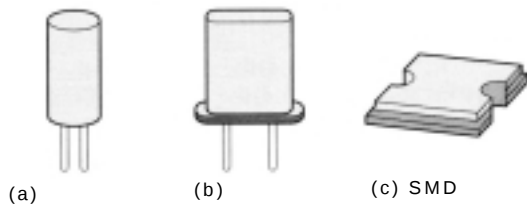
SMD

CX-49F, CX-49G
(HC-49/U-S)

가

SMD

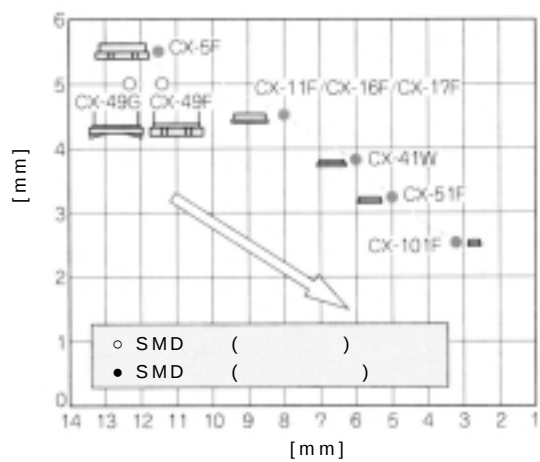
가



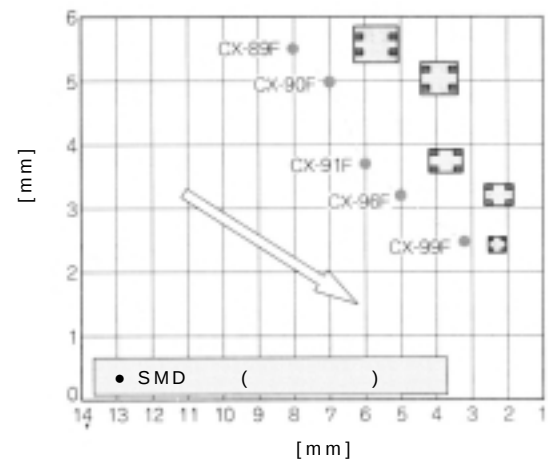
7.

8 가

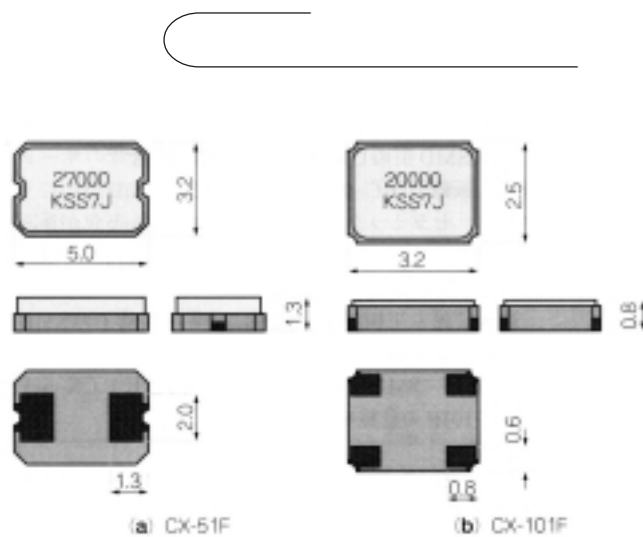
9



8. 가 SMD



9. SMD



	CX-51F	CX-101F
[MHz]	20~47	
[]	-10~+60	
(@25)	$\pm 30, \pm 50, \pm 100 (\times 10^{-6})$	
	$\pm 30, \pm 50, \pm 100 (\times 10^{-6})$	
[pF]	12	
가 [Ω]	100	
[mm]	5.0×3.2×1.3	3.2×2.5×0.8

(c)

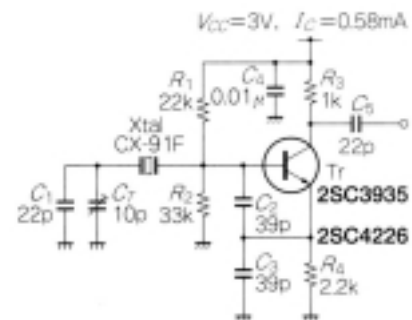
10. CX-51F CX-101F

1.

1.		_____ MHz
2.		
3.		_____
4.		_____ $\times 10^{-6}$ MAX. (@25 °C)
5.		_____ $\times 10^{-6}$ _____ °C
6.	가	_____ □ MAX.
7.	(C _L)	_____ pF
8.		_____ mW
9.	(C _O)	_____ pF MAX.
10.		_____
11.		_____
12.		_____

11.

(10M ~ 40MHz)



SMD , CX-51F 가

CX-101F .

(4)

25

가 . 1

(1)

가

(5)

. AT

, 3

(2) ()

2

(3)

가,

가
(次數)

(6) 가

가

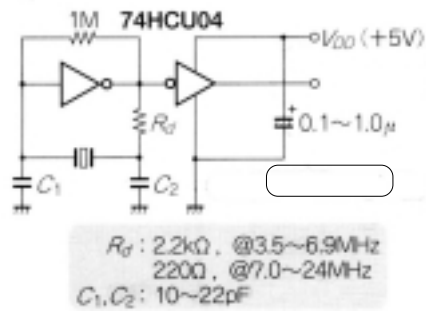
‘ JIS C6701(9) ’ 가

가

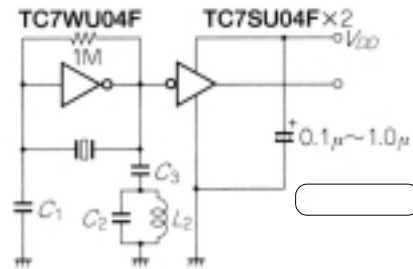
가

(7)

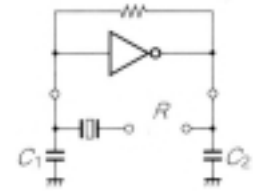
3/



12. CMOS IC



13. CMOS IC



14.

2.

[MHz]	[Ω]
3.5 ~ 4.5	1.5 k
4.6 ~ 6.0	1.0 k
6.1 ~ 10.0	750
10.1 ~ 14.0	500
14.1 ~ 20.0	400

가

가

(11)

12p~16pF가

(8)

kHz

MHz

가

(12)

가

가

가

가

(9)

 C_0

AT

 C_0

가

(10)

가

11, 13

()

(1)

가

(2)

(14)

가

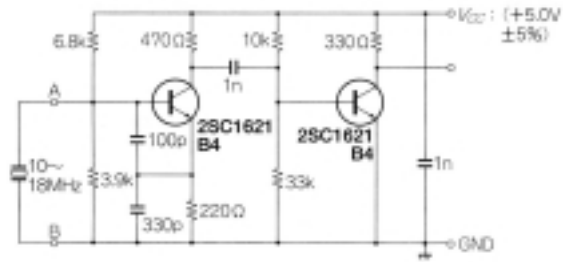
가

2

가

5

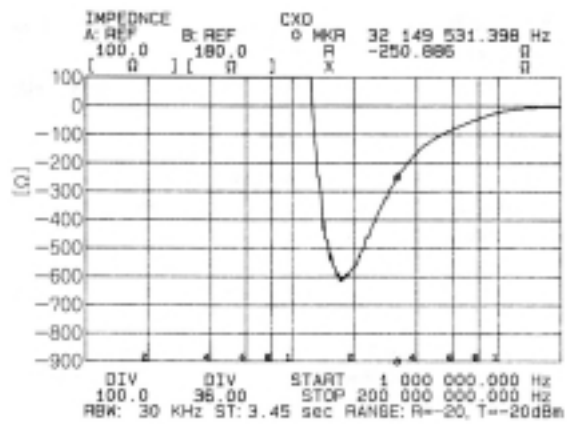
<大隅 明>



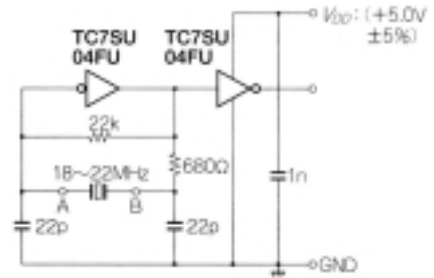
15.



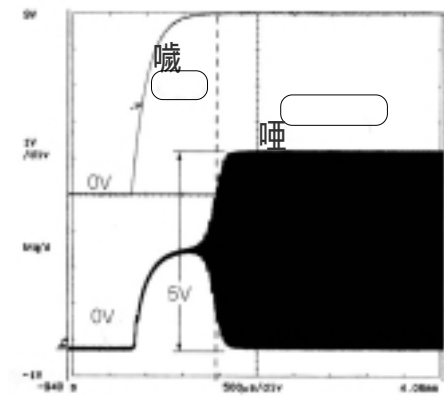
17. 가



19. HCMOS IC



16.



18.

3.

	가	
	SPXO	VCXO
	TCXO	VC-TCXO
	DTCXO	VC-DTCXO
	OCXO	VC-OCXO

가

$$\pm 1 \times 10^{-4} \sim \pm 2 \times 10^{-9}$$

15, 16

가

가

17

가

가 L_e 가 R_e 가 C_i 가 ()

3/

) R_i

$$\omega L_e - \frac{1}{\omega C_i} = 0$$

$$f = 1/(2\pi\sqrt{L_e C_i})$$

 R_e $|R_i|$ (1)

 R_i 가 R_e (2)

 R_i R_e (3)

3~10

18

19 HCMOS IC

 R_i

4

가

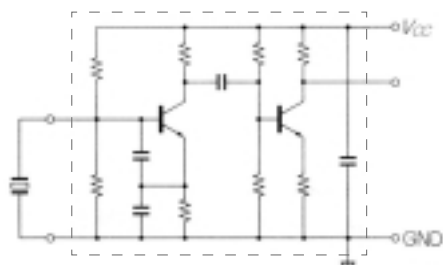
가

Q

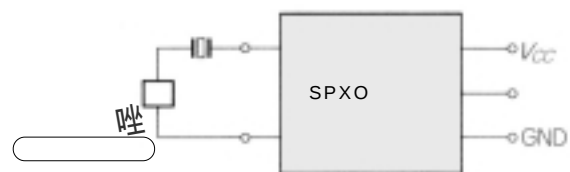
가 $\pm 3 \times 10^{-6} \sim \pm 100 \times 10^{-6}$

4.

	[]	[× 10 ⁻⁶]															
SPXO VCXO	0 ~ + 50												± 3	± 5	± 10	± 50	± 100
	- 10 ~ + 60													± 5	± 10	± 50	± 100
	- 20 ~ + 70														± 10	± 50	± 100
	- 30 ~ + 80															± 50	± 100
	- 40 ~ + 90															± 50	± 100
	0 ~ + 70														± 10	± 50	± 100
TCXO	0 ~ + 50								± 0.3	± 0.5	± 1	± 2					
	- 10 ~ + 60									± 0.5	± 1	± 2	± 3				
	- 20 ~ + 70										± 1	± 2	± 3	± 5			
	- 30 ~ + 80											± 2	± 3	± 5			
	- 40 ~ + 90											± 2	± 3	± 5			
OCXO	0 ~ + 50	± 0.002	± 0.005	± 0.01	± 0.02	± 0.05											
	- 10 ~ + 60		± 0.005	± 0.01	± 0.02	± 0.05	± 0.1										
	- 20 ~ + 70			± 0.01	± 0.02	± 0.05	± 0.1	± 0.2									

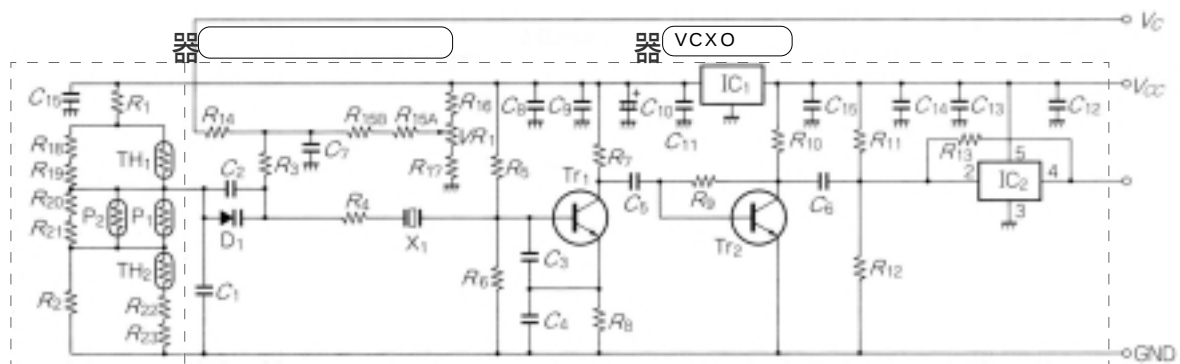


20. SPXO

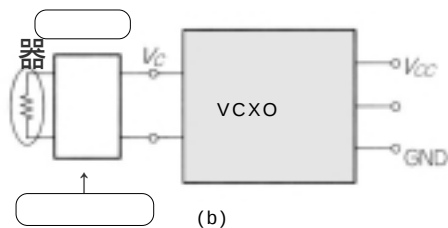


21.

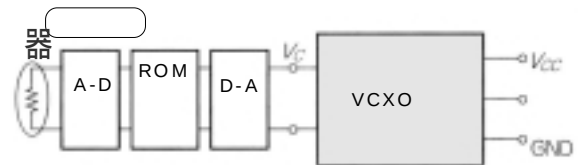
TCXO



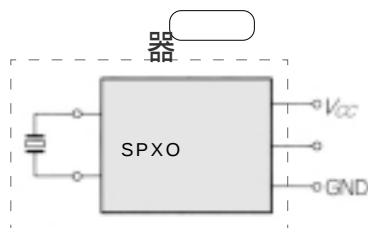
(a) TCXO



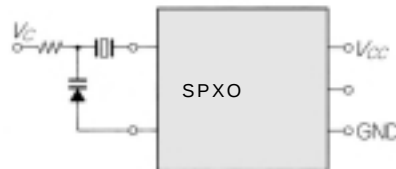
TCXO



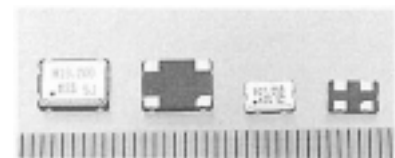
DTCXO



OCXO

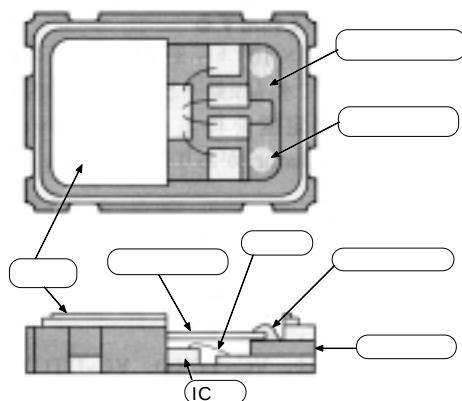


VCXO



1. SMD

SPXO



26.

가 $\pm 0.3 \times 10^{-6} \sim \pm 5 \times 10^{-6}$

TCXO

(Temperature Compensated Crystal Oscillator)

. TCXO

(21)

C_L

(22)

가

VCXO(Voltage Controlled Crystal Oscillator)

가

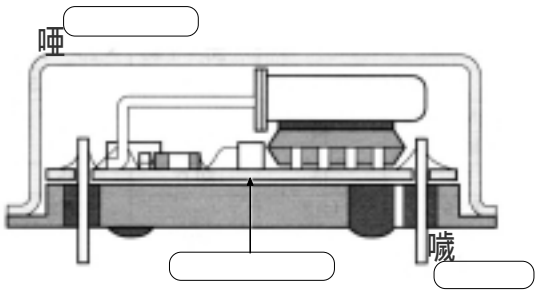
SPXO

(Simple Packaged Crystal Oscillator) (

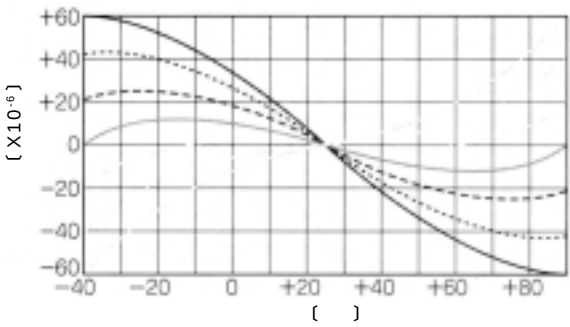
20)

5. SMD [FXO , (株)]

			FXO-31F	FXO-31FH	FXO-31FT	FXO-31FL	FXO-32F	FXO-32FL	FXO-34F	FXO-34FL	FXO-37F	FXO-37FL
	f	MHz	1.8 ~ 50				8 ~ 32	50 ~ 100	8 ~ 32	50 ~ 100	100 ~ 125	50 ~ 100
	df	$\times 10^{-6}$	± 100				± 30		± 30		± 100	
	t_o	$^{\circ}\text{C}$	$-10 \sim +70$				$-10 \sim +60$		$-30 \sim +85$		$0 \sim +70$	
	t_x	$^{\circ}\text{C}$	$-55 \sim +125$				$-20 \sim +80$		$-30 \sim +85$		$-20 \sim +80$	
	V_{DD}	V	$+5 \pm 0.5$			$+3.3 \pm 0.3$	$+5 \pm 0.25$	$+3.3 \pm 0.165$	$+5 \pm 0.25$	$+3.3 \pm 0.165$	$+5 \pm 0.25$	$+3.3 \pm 0.15$
	I_{DD}	mA max	25	25 (1.8 ~ 15 MHz)		20	12	8	12	10	50	25
			—	30 (15.1 ~ 32 MHz)		—	—	—	—	—	—	—
			—	45 (32.1 ~ 50 MHz)		—	—	—	—	—	—	—
	C_L	pF	15	50		20	15				25	15
	IC	TTL	LS10	10		5	2	1	2	1	10	5
	V_{OV}	Vmin	4.5				2.97	4.5	2.97	4.0		2.8
	V_{OL}	Vmax	0.5			0.4	0.5					
	D	%	40 ~ 60									
(symmetry)	—	V	2.5	1.4	1.65	2.5	1.5	2.5	1.65	2.5	1.65	
	t_r/t_f	ns max	10	6		12	16	12	16	7		
	—											



27.



28. SPXO

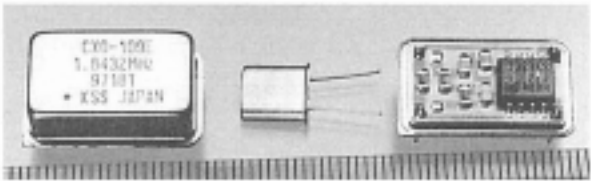
ROM , DTCXO (Digital processing Temperature Compensated Crystal Oscillator)가 (23).

- 가 $\pm 0.002 \times 10^{-6} \sim \pm 0.2 \times 10^{-6}$

OCXO(Oven Controlled Crystal Oscillator)가 (24).

- 가
- 가

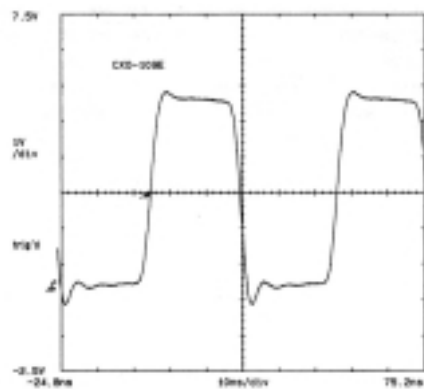
25 VCXO , VC-TCXO, VC-DTCXO



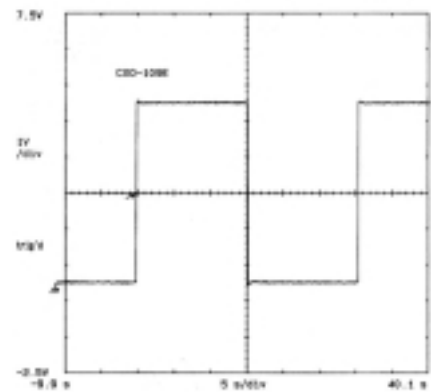
2. SPXO

VCXO VC-OCXO (PLL)

가



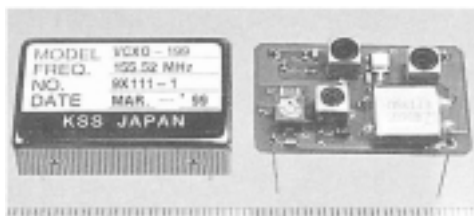
29.
(f=19MHz, 50pF)



30.
(f=32.768kHz, 50pF)

6. [CXO]

			CXO-072D	CXO-106B	CXO-108	CXO-109E	CXO-109H	CXO-199	CXO-203
	f	MHz	4.9~20.8	40~100	80~200	0.001~80	0.5~50	30~160	0.032768
	df	$\times 10^{-6}$	± 5	± 100			± 20		± 80
	t_e	$^{\circ}\text{C}$	0~+60	-10~+70					-10~+50
	t_i	$^{\circ}\text{C}$	-30~+85	-20~+85				-20~+80	-20~+85
	V_{DD}	V	+5 $\pm$ 0.25	+5 $\pm$ 0.5	-5.2 $\pm$ 0.25	+5 $\pm$ 0.25		-5.2 $\pm$ 0.25	+5 $\pm$ 0.5
(symmetry)	I_{DD}	mA max	20	60		25(0.001M~20MHz) 60(20.1M~80MHz)	45	40	0.15
	C_L	pF	—	20	—	50	15	50 Ω	15
	IC	TTL	2	AS10	10KH ECL	LS 5	LS 2	—	LS 2
	V_{out}	Vmin	2.4	3.0	-1.02~-0.74	4.5		0 dBm	4.5
	V_{OL}	Vmax	0.4	0.5	-1.95~-1.60	0.5		—	0.5
	D	%	40~60					—	—
	—	V	1.4	1.3	-1.29	2.5		—	2.5
	t_r/t_f	ns max	10	5	3.5	10		—	300
	—	—							



3. VCXO

26

IC

FXO

{ (株) }

FXO

0.01μF

CMOS

TTL

IC

가

3

5

FXO-61F

3.2×5.0×1.

● SPXO

SMD

(1)

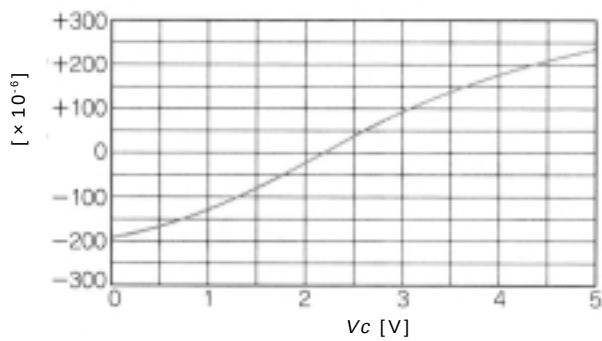
가

5.0×7.0×1.8mm

3/

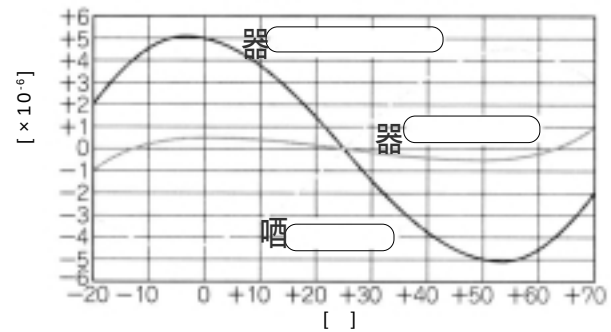
7. VCXO/VC-CXO

			VC-CXO-072E	VC-CXO-072G	VC-CXO-072H	VCXO-078B	VCXO-105N	VCXO-190	VCXO-199
	f	MHz	11 ~ 34		27 ~ 60	32 ~ 100	1.5 ~ 33	14 ~ 29	30 ~ 160
	df	$\times 10^{-4}$	± 40				± 30	± 30	± 40
	t_o	$^{\circ}\text{C}$	$-20 \sim +70$			$-10 \sim +60$	$-20 \sim +70$	$-10 \sim +60$	$-10 \sim +75$
	t_s	$^{\circ}\text{C}$	$-40 \sim +85$			$-40 \sim +75$	$-40 \sim +85$	$-30 \sim +80$	$-20 \sim +80$
	V_{DD}	V	$+5 \pm 0.25$						
가	I_{DD}	mA max	20	25		40	27	15	40
	df	$\times 10^{-4}$	± 100	± 150	± 100	± 70	± 100	± 50	± 120
	V_C	V	$+2.5 \pm 2.5$	$+2.5 \pm 2.0$	$+2.5 \pm 2.5$	$+2.5 \pm 2.0$		$+2.5 \pm 2.5$	
	C_L	pF	—	15		—	15		50 Ω
	IC	TTL	1	LS 2	AS 2	1	—	LS 2	—
	V_{OH}	Vmin	3.0	4.5		3.0	4.5		0 dBm
	V_{OL}	Vmax	0.4	0.5		0.4	0.5		—
	D	%	40 ~ 60			30 ~ 70	40 ~ 60		—
	—	V	1.4	2.5		1.4	2.5		—
	t_r/t_f	ns max	10	5		10		5	—
	—	—							



31. VC-CXO-072G

가



32. TCXO

-

2mm FXO-31F 30%

(2)

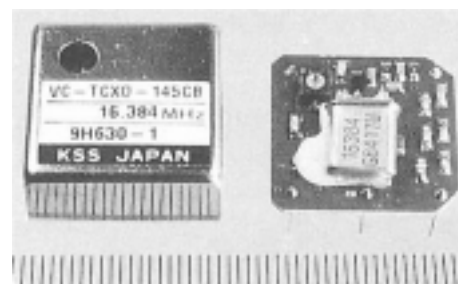
13.08 × 20.8 ×

8.26mm

27

UM-1

IC



4. TCXO

가 가

SPXO

가

10MHz

80MHz

. AT

10MHz

가

28

AT (

3

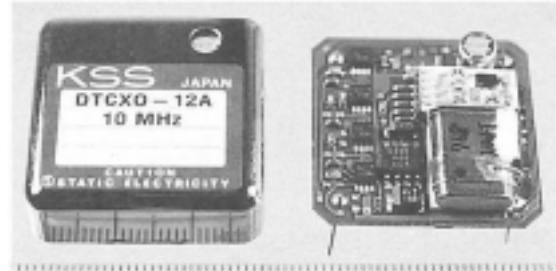


8. VC-TCXO-145CB

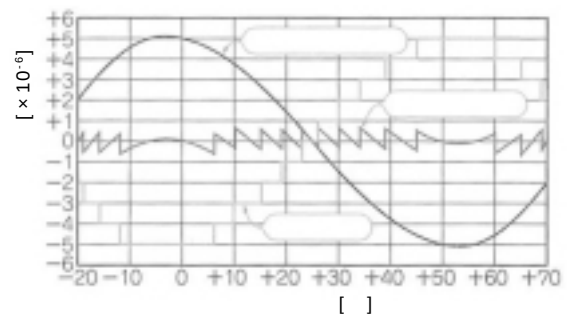
VC-TCXO-145CB	
	2 MHz ~ 30 MHz
	-10℃ ~ +60℃
	-40℃ ~ +80℃
	$\pm 1 \times 10^{-6}$ max./-10℃ ~ +60℃
	$\pm 1 \times 10^{-6}$ max./year
	$\pm 0.2 \times 10^{-6}$ max./+5.0V $\pm 5\%$
	$\pm 10 \times 10^{-6}$ min./+2.5V ± 2.0 V ()
	$\pm 3 \times 10^{-6}$ max./ (對)
	+5.0V $\pm 5\%$
	20 mA max.
	$V_{DD} : +4.5$ V min. $V_{DD} : +0.5$ V max. ($V_{CC} = +5.0$ V)
	CMOS (15pF)
	40 ~ 60% @ +2.5 V ()
	10 k Ω min.

9. DTCXO-12A

DTCXO-12A	
	1 MHz ~ 32 MHz
	-40 ~ +85℃
	-35 ~ +85℃
	$\pm 0.1 \times 10^{-6}$ max./-35 ~ +85℃
	$\pm 0.5 \times 10^{-6}$ max./year
	$\pm 0.05 \times 10^{-6}$ max./5 V $\pm 5\%$
	$\pm 0.7 \times 10^{-6}$ min.
	30 mA max./5 V
	CMOS
	45 ~ 55 %/1 ~ 15 MHz
	30 ~ 70 %/15 ~ 32 MHz
	-80 dB max.



5. DTCXO



33. DTCXO



6. OCXO

0.8MHz
CT DT
2 3
AT 가
10~30MHz AT
IC
CXO-109E
1kHz~10MHz IC
29
19MHz , 30
32.768kHz
6

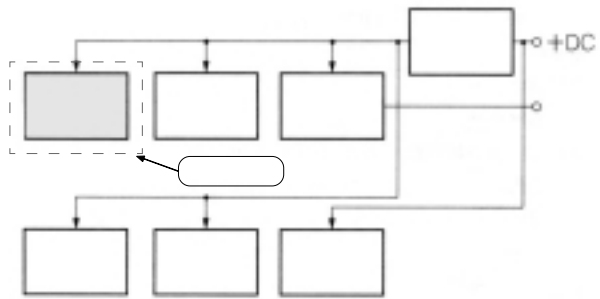
HCMOS, AS TTL, 10KH-ECL IC
50 Ω 0dBm

• VCXO (3)

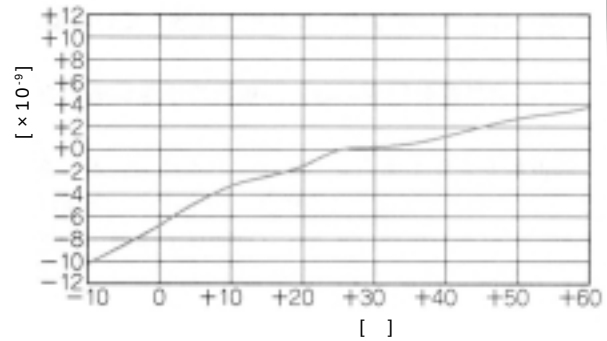
VCXO-190 SMD
SPXO
, UM-1 IC

UM-1 가

3/



34. OCXO



35. OCXO-108B(@5MHz)

31 VC-CXO-072G
가
7
VCXO-105N,
VC-CXO-072H VCXO-
199 HCMOS AS TTL IC
가 50Ω 0dBm

• TCXO(4)
TCXO
(VCXO)

HCMOS TTL
32

8 VC-TCXO-145CB

• DTCXO(5)

DTCXO

(VCXO)

A-D
ROM D-A

HCMOS TTL

33

가

ROM

ROM

33

가

$\pm 0.1 \times 10^{-6}$

9 DTCXO-12A

• OCXO(6)

OCXO

가가

HCMOS TTL

34

+70

AT

SC

10. OCXO-108B

OCXO-108B	
5 MHz	
-20 ~ +70 °C	
0 ~ +60 °C	
$\pm 1.5 \times 10^{-8}$ max./0 ~ +60 °C	
$\pm 2 \times 10^{-8}$ max./year	
$\pm 5 \times 10^{-9}$ max./+12.0 V $\pm 5\%$	
$\pm 1 \times 10^{-7}$ min.	
	+12.0 V $\pm 5\%$
	500 mA max.
	TTL
	TTL ($\dots$ = 2)
30	$\pm 2 \times 10^{-8}$

35

10 OCXO-108B

11

가 . —

가

•

가

()

(1)

(2)

(3) 가 , , 가

(4) ,

(5)

(6)

()

(1) 가

(2) 가

(3)

•

(0.

2 ~ 0.5A)

OCXO

가 0.5A OCXO

1Ω

5V

0.5V

가

4.

5V OCXO

가

•

가

0.1~100

μF

가 IC

가

IC

• VCXO

가

VCXO

가

가

가

3/

11.

1.		_____ MHz
2.		
(1)		$\pm$ _____ $\times 10^{-6}$ max.
		- _____ ~ + _____ $^{\circ}\text{C}$
(2)		$\pm$ _____ $\times 10^{-6}$ max.
		+ _____ VDC $\pm$ _____ %
(3)		$\pm$ _____ $\times 10^{-6}$ max.
		_____ Ω , _____ pF $\pm$ _____ %
(4)		$\pm$ _____ $\times 10^{-6}$ max./
3.	가	$\pm$ _____ $\times 10^{-6}$ min.
4.		$\pm$ _____ ~ $\pm$ _____ $\times 10^{-6}$
		+ _____ V $\pm$ _____ V
5.		
(1)		(TTL, HCMOS),
		2 _____ dB, 3 _____ dB
(2)		_____ V rms, _____ Vpp
		Voh _____ V, Vol _____ V
(3)		_____ Ω , _____ pF
		LS-TTL _____,
		HCMOS _____
6.		+ _____ VDC $\pm$ _____ % _____ mA max
7.		
(1)		- _____ ~ + _____ $^{\circ}\text{C}$
(2)		- _____ ~ + _____ $^{\circ}\text{C}$
(3)		_____ mm,
		_____ ~ _____ Hz
(4)		_____ cm
8.		
9.		
10.		

TTL 가
가
가

• EMC가

가

가

• TTL 가 . <小柳津 泰夫>

